

High power PNP epitaxial planar bipolar transistor

Features

- High breakdown voltage V_{CEO} = -250 V
- Complementary to 2STC5948
- Typical f_t = 25 MHz
- Fully characterized at 125 °C

Application

Audio power amplifier

Description

The device is a PNP transistor manufactured using new BiT-LA (Bipolar transistor for linear amplifier) technology. The resulting transistor shows good gain linearity behaviour.

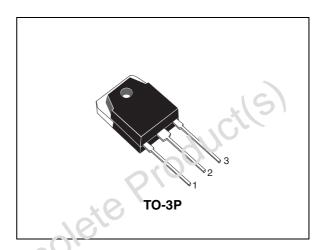


Figure 1. Internal schematic diagram

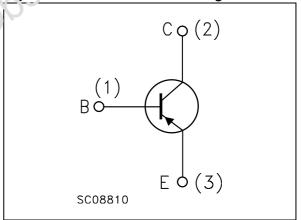


Table 1. Device summary

Order code	Marking	Package	Packaging
2STA2120	2STA2120 2STA2120		Tube

Electrical ratings 2STA2120

1 Electrical ratings

Table 2. Absolute maximum rating

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-base voltage (I _E = 0)	-250	V
V _{CEO}	Collector-emitter voltage (I _B = 0)	-250	V
V _{EBO}	Emitter-base voltage ($I_C = 0$)	-6	V
I _C	Collector current	-17	Α
I _{CM}	Collector peak current (t _P < 5 ms)	-34	.1
P _{TOT}	Total dissipation at T _C = 25 °C	200	W
T _{stg}	Storage temperature	· 65 to 150	°C
TJ	Max. operating junction temperature	150	°C

Table 3. Thermal data

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Symbol	Parameter	16,	Value	Unit
R _{thi-case}	Thermal resistance junction-case	max	0.625	°C/W

2 Electrical characteristics

(T_{case} = 25 °C; unless otherwise specified)

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector cut-off current $(I_E = 0)$	V _{CB} = -250 V			-5	μΑ
I _{EBO}	Emitter cut-off current (I _C = 0)	V _{EB} = -6 V			-5	μA
V _{(BR)CEO} ⁽¹⁾	Collector-emitter breakdown voltage (I _B = 0)	I _C = -50 mA	-250			V
V _{(BR)CBO}	Collector-base breakdown voltage (I _E = 0)	I _C = -100 μA	-250	gin,		V
V _{(BR)EBO} ⁽¹⁾	Emitter-base breakdown voltage ($I_C = 0$)	I _E = -1 mA	-6			V
V _{CE(sat)} (1)	Collector-emitter saturation voltage	I _C = -8 A			-3	V
V _{BE} (1)	Base-emitter voltage	I _C = -7 A V _{CE} = -5 V			-1.5	V
h _{FE}	DC current gain	$I_C = 1 A$ $V_{CE} = -5 V$ $I_C = -7 A$ $V_{CE} = -5 V$	80 35		160	
f _T	Transition frequency	$I_C = -1 A$ $V_{CE} = -5 V$		25		MHz

^{1.} Pulsed duration = 300 μs, duty cycle ≤1.5%

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Electrical characteristics 2STA2120

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

Figure 3. Derating curve

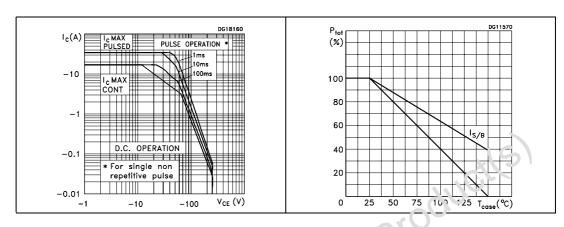


Figure 4. Output characteristics

Figure 5. Document gain

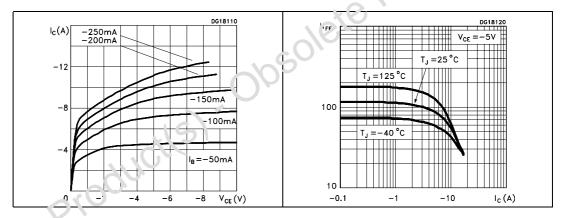
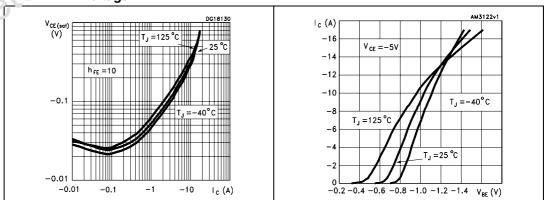


Figure 3. Collector-emitter saturation voltage

Figure 7. Base-emitter voltage



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3 Package mechanical data

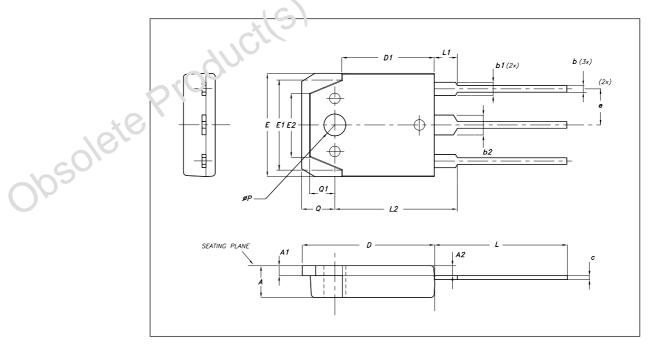
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DIM.		mm.	
DIIVI.	MIN.	TYP	MAX.
Α	4.6		5
A1	1.45	1.50	1.65
A2	1.20	1.40	1.60
b	0.80	1	1.20
b1	1.80		2.20
b2	2.80		3.20
С	0.55	0.60	(.75
D	19.70	19.90	20.13
D1		13.90	
E	15.40		15.80
E1		13.60	
E2		9.60	
е	5.15	5.45	5.75
L	19.50	20	20.50
L1		00	
L2	18.20	13.40	18.60
Р	3.10	25	3.30
Q		5	
Q1		3.80	



2STA2120 Revision history

4 Revision history

Table 5. Document revision history

Date	Revision	Changes
23-Nov-2007	1	Initial release
09-May-2008	2	Added new graphics.
07-Nov-2008	3	Document status promoted from preliminary data to datasheet.

Obsolete Product(s)

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